

## Vertical Deflection Booster for Slim CRTs

DATASHEET

### OVERVIEW

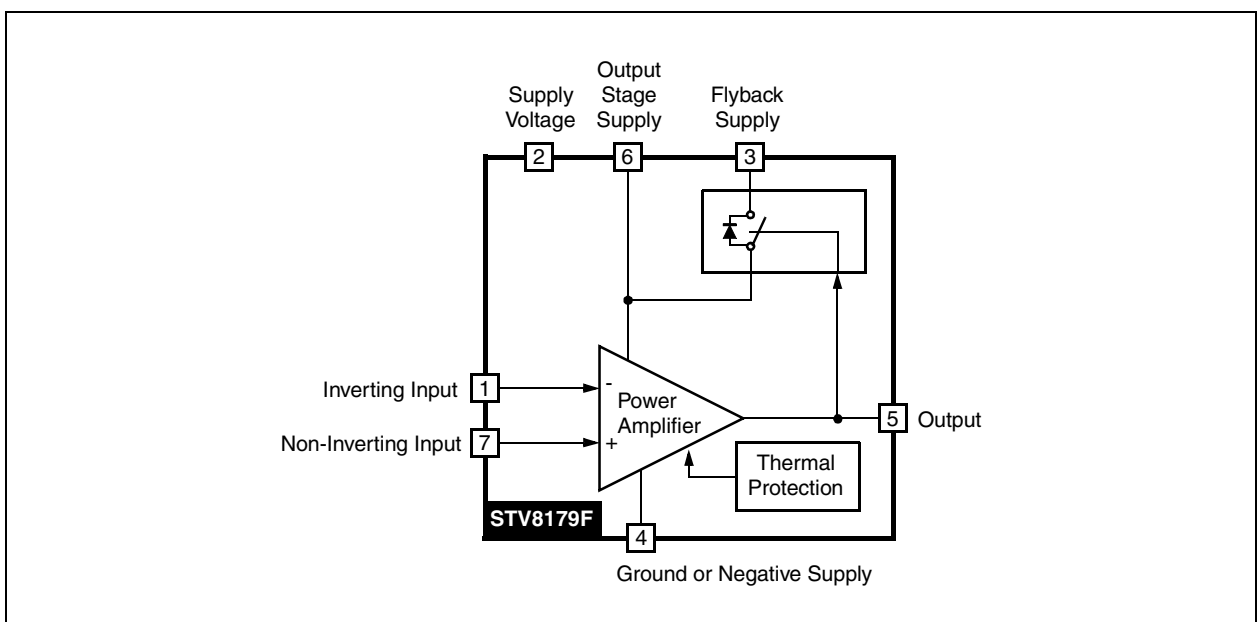
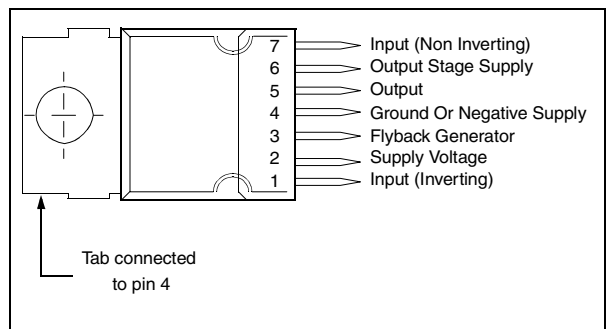
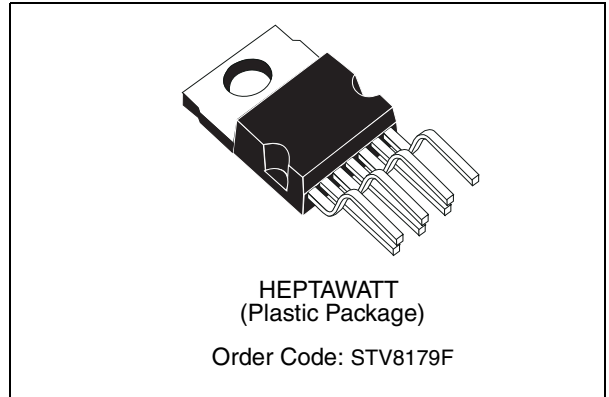
- Power Amplifier
- Thermal Protection
- Output Current up to  $3.6A_{PP}$
- Flyback Voltage up to 90V (on Pin 5)
- Suitable for DC Coupling Application
- External Flyback Supply

### DESCRIPTION

Designed for monitors and high performance TVs, the STV8179F vertical deflection booster can handle flyback voltages of up to 90V. In addition, it is possible to have a flyback voltage which is more than double that of the supply (Pin 2). This allows decreasing power consumption or decreasing the flyback time for a given supply voltage.

The STV8179F operates with supplies of up to 42V and outputs up to  $3.6A_{PP}$  to drive the yoke.

The STV8179F is offered in a HEPTAWATT package.



Rev. 3

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# 1 Absolute Maximum Ratings

Symbol	Parameter	Value	Unit
$V_S$	Supply Voltage (Pin 2) (see note 1)	50	V
$V_6$	Flyback Peak Voltage (Pin 6) (see note 1)	120	V
$V_1, V_7$	Amplifier Input Voltage (Pins 1-7) (see note 1)	-0.3, + $V_S$	V
$I_O$	Maximum Output Peak Current (see notes 2 and 3)	3.0	A
$I_3$	Maximum Sink Current ( $t < 1$ ms)	3.0	A
$I_3$	Maximum Source Current ( $t < 1$ ms) (in the diode, see Block Diagram) (see note 2)	3.0	A
$V_{ESD}$	ESD Susceptibility: EIAJ Norm (200pF discharged through 0 $\Omega$ )	300	V
$V_3-V_2$	Voltage Difference between Flyback Supply and Supply Voltage	50	V
$T_{OPER}$	Operating Ambient Temperature	-20, +75	°C
$T_{STG}$	Storage Temperature	-40, +150	°C
$T_J$	Junction Temperature	+ 150	°C

Note: 1 Versus Pin 4.

2 The output current can reach 6A peak for  $t \leq 10\mu\text{s}$  (up to 120 Hz)

3 Provided SOAR is respected (see Figures 3 and 4).

# 2 Thermal Data

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction-Case Thermal Resistance Max.	3	°C/W
$T_T$	Temperature for Thermal Shutdown	150	°C
$T_{JR}$	Recommended Max. Junction Temperature	120	°C

### 3 Electrical Characteristics

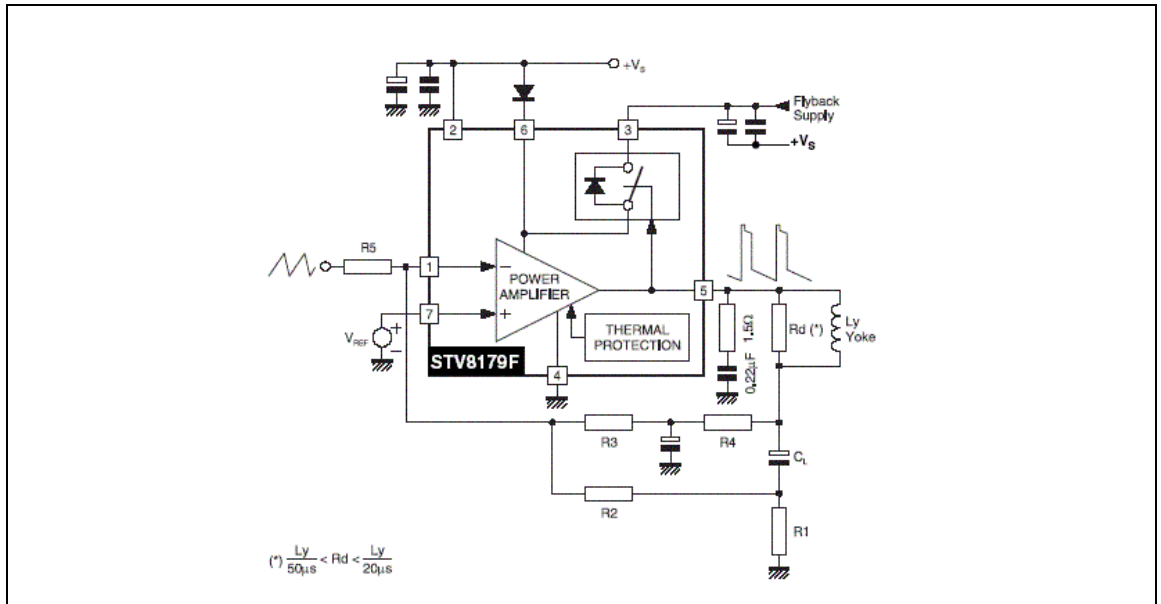
( $V_S = 42V$ ,  $T_A = 25^\circ C$ , unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_S$	Operating Supply Voltage Range	Versus Pin 4	10		42	V
$V_{3M}$	Operating Flyback Supply Voltage ( $V_{3M} \leq V_S + 50V$ )	Versus Pin 4	$V_S$		90	V
$I_2$	Pin 2 Quiescent Current	$I_3 = 0$ , $I_5 = 0$		13	20	mA
$I_6$	Pin 6 Quiescent Current	$I_3 = 0$ , $I_5 = 0$	7	12	35	mA
$I_o$	Max. Operating Peak Output Current	Refer to Note 1			1.8	A
$I_1$	Amplifier Bias Current	$V_1 = 22V$ , $V_7 = 23V$		-0.15	- 1	$\mu A$
$I_3$	Flyback current during scanning period	$V_{FLYBACK} = 100V$		2.0	5.0	mA
$I_7$	Amplifier Bias Current	$V_1 = 23V$ , $V_7 = 22V$		-0.15	- 1	$\mu A$
$V_{IO}$	Offset Voltage				7	mV
$\Delta V_{IO}/dt$	Offset Drift Versus Temperature			- 10		$\mu V/^\circ C$
GV	Voltage Gain		80			dB
$V_{5L}$	Output Saturation Voltage to GND (Pin 4)	$I_5 = 1.8A$		1.35	2.2	V
$V_{5H}$	Output Saturation Voltage to Supply (Pin 6)	$I_5 = -1.8A$		2.2	3.0	V
$V_{D5-6}$	Diode Forward Voltage between Pins 5-6	$I_5 = 1.8A$		1.8	2.3	V
$V_{D3-6}$	Diode Forward Voltage between Pins 3-6	$I_3 = 1.8A$		2.3	3.3	V
$V_{3-6}$	Voltage Drop between Pin 3-6 (2nd part of flyback)	$I_3 = - 1.8A$		3.6	4.2	V
$V_{5Th}$	Threshold voltage for triggering Flyback			$V_S + V_d$		V

Note: 1 Provided SOA for the output transistors is respected (see Figures 3 and 4).

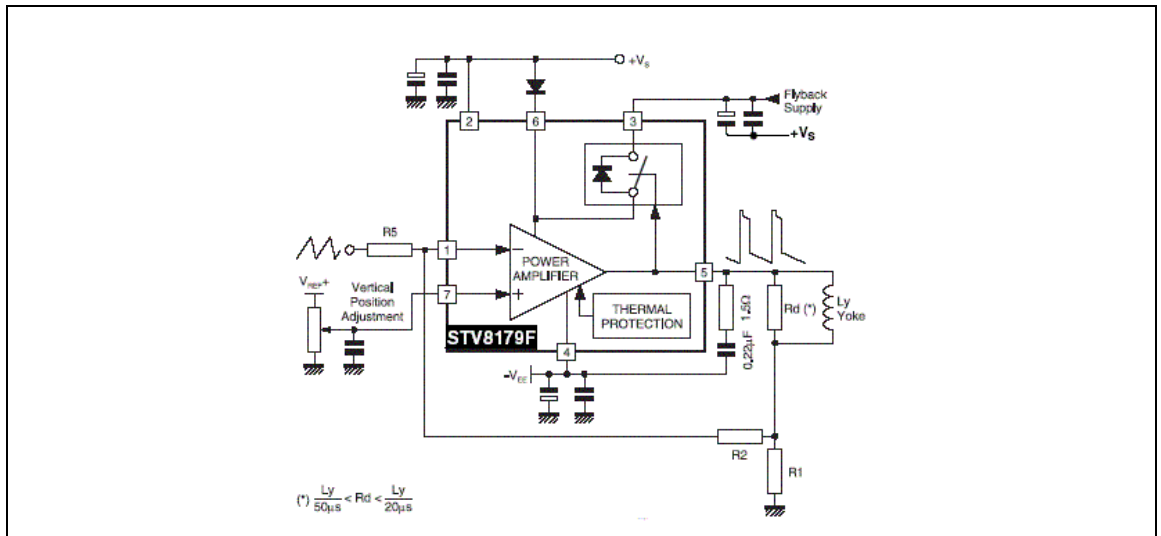
# 4 Application Circuits

Figure 1: AC Coupling



Note: To prevent spurious voltages during power-on/power-off phases, you must refer the flyback voltage to +Vs rather than to Ground.

Figure 2: DC Coupling



Note: To prevent spurious voltages during power-on/power-off phases, you must refer the flyback voltage to +Vs rather than to Ground.

Figure 3: Output Transistor SOA (for Secondary Breakdown)

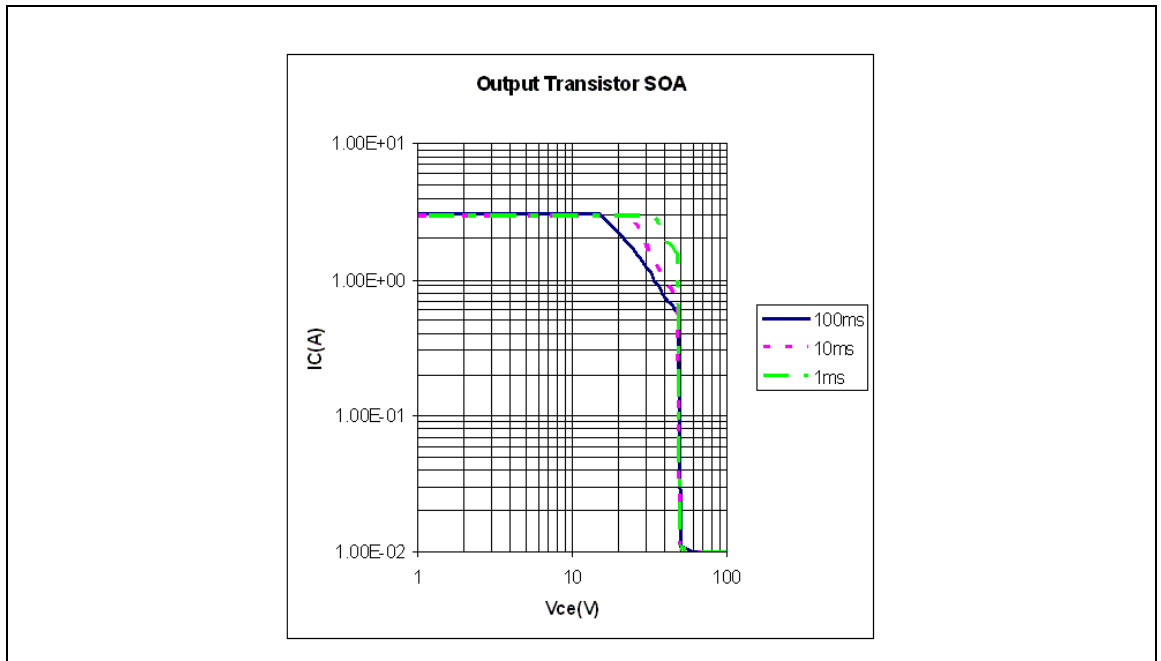
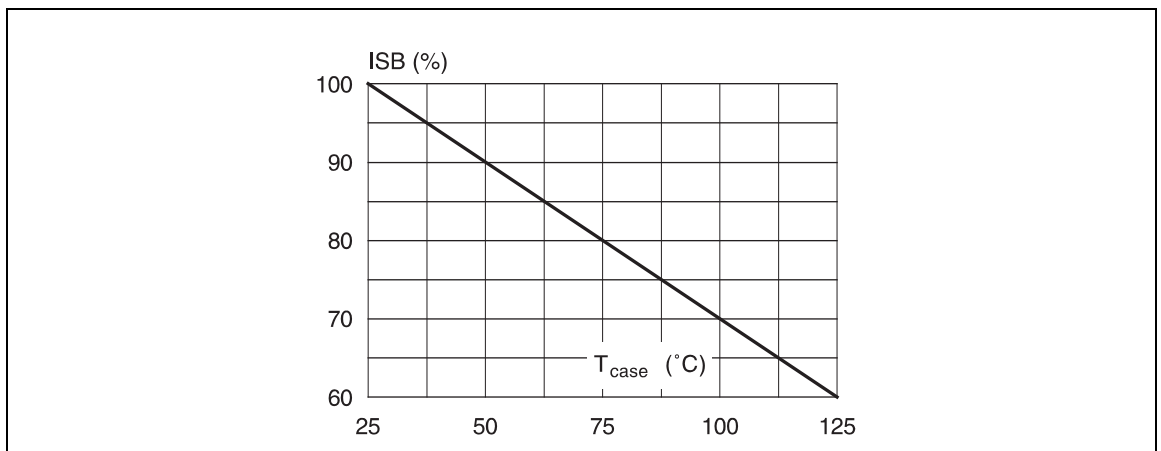


Figure 4: Secondary Breakdown Temperature De-rating Curve (ISB = Secondary Breakdown Current)



## 5 Package Mechanical Data

Figure 5: 7-pin Plastic Heptawatt Package

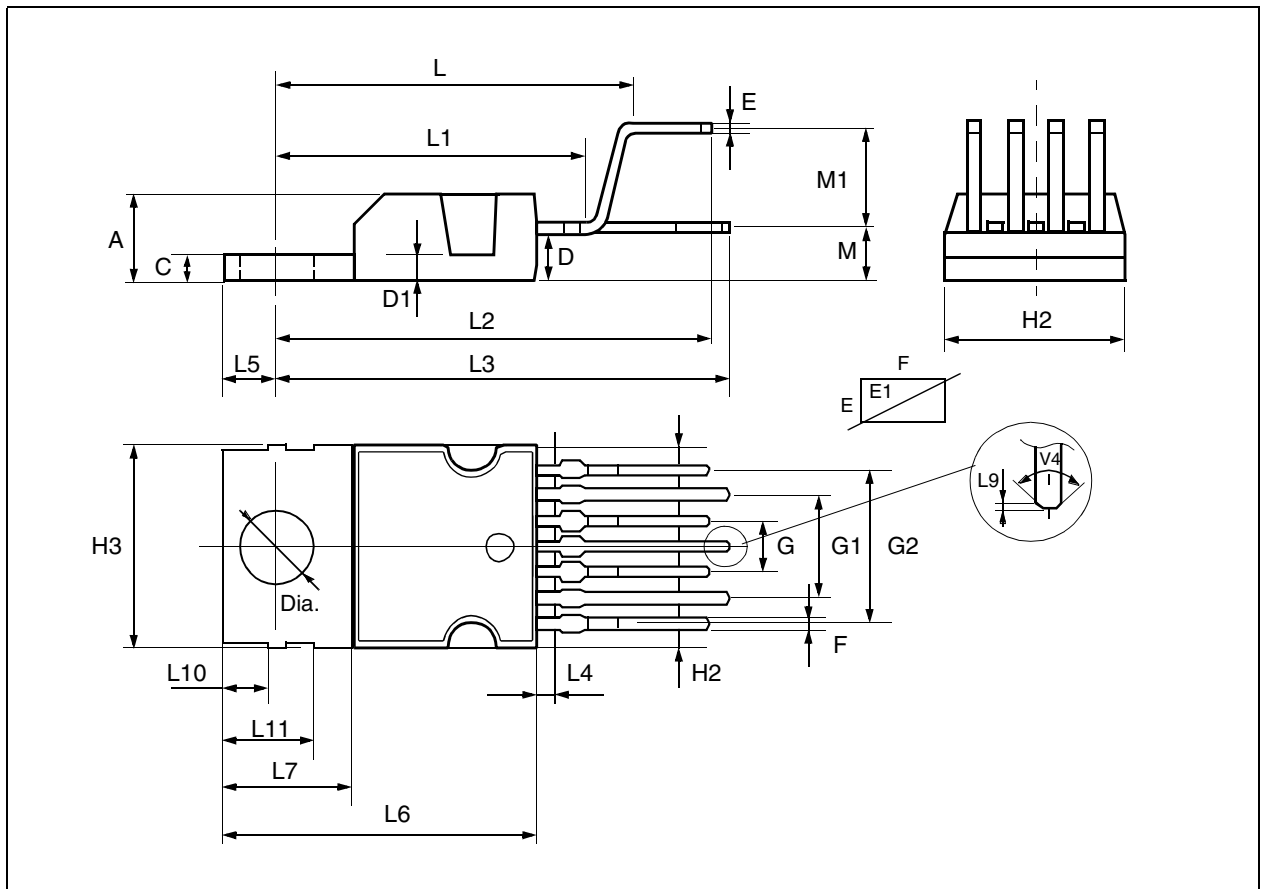


Table 1: Heptawatt Package

Dim.	mm			inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			4.8			0.189
C			1.37			0.054
D	2.40		2.80	0.094		0.110
D1	1.20		1.35	0.047		0.053
E	0.35		0.55	0.014		0.022
E1	0.70		0.97	0.028		0.038
F	0.60		0.80	0.024		0.031
G	2.34	2.54	2.74	0.095	0.100	0.105
G1	4.88	5.08	5.28	0.193	0.200	0.205
G2	7.42	7.62	7.82	0.295	0.300	0.307
H2			10.40			0.409
H3	10.05		10.40	0.396		0.409
L	16.70	16.90	17.10	0.657	0.668	0.673

Table 1: Heptawatt Package (continued)

Dim.	mm			inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
L1		14.92			0.587	
L2	21.24	21.54	21.84	0.386	0.848	0.860
L3	22.27	22.52	22.77	0.877	0.891	0.896
L4			1.29			0.051
L5	2.60	2.80	3.00	0.102	0.110	0.118
L6	15.10	15.50	15.80	0.594	0.610	0.622
L7	6.00	6.35	6.60	0.0236	0.250	0.260
L9		0.20			0.008	
L10	2.10		2.70	0.082		0.106
L11	4.30		4.80	0.169		0.190
M	2.55	2.80	3.05	0.100	0.110	0.120
M1	4.83	5.08	5.33	0.190	0.200	0.210
V4	40 (Typ.)					
Dia.	3.65		3.85	0.144		0.152



**Notes:**

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